

Bhanu B Upadhyay

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Ti/Au/Al/Ni/Au low contact resistance and sharp edge acuity for highly scalable AlGaIn/GaN HEMTs. IEEE Electron Device Letters, 2018, , 1-1.	2.2	27
2	Surface stoichiometry modification and improved DC/RF characteristics by plasma treated and annealed AlGaIn/GaN HEMTs. Solid-State Electronics, 2018, 141, 1-6.	0.8	15
3	Al ₂ O ₃ formed by post plasma oxidation of Al as a Gate dielectric for AlGaIn/GaN MIS-HEMTs. Applied Surface Science, 2019, 481, 219-225.	3.1	13
4	Reduced Contact Resistance and Improved Transistor Performance by Surface Plasma Treatment on Ohmic Regions in AlGaIn/GaN HEMT Heterostructures. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700656.	0.8	12
5	Impact of Relative Gate Position on DC and RF Characteristics of High Performance AlGaIn/GaN HEMTs. IEEE Transactions on Electron Devices, 2020, 67, 4141-4146.	1.6	11
6	Source extension region scaling for AlGaIn/GaN high electron mobility transistors using non-alloyed ohmic contacts. Solid-State Electronics, 2016, 122, 70-74.	0.8	10
7	Performance improvement and better scalability of wet-recessed and wet-oxidized AlGaIn/GaN high electron mobility transistors. Solid-State Electronics, 2017, 131, 39-44.	0.8	7
8	Epi-Gd ₂ O ₃ /f-MOSHEMT: A Potential Solution Toward Leveraging the Application of AlGaIn/GaN/Si HEMT With Improved <i>I</i> _{ON} / <i>I</i> _{OFF} Operating at 473 K. IEEE Transactions on Electron Devices, 2021, 68, 2653-2660.	1.6	6
9	Improvements From SiC Substrate Thinning in AlGaIn/GaN HEMTs: Disparate Effects on Contacts, Access and Channel Regions. IEEE Electron Device Letters, 2021, 42, 684-687.	2.2	4
10	Evolution of field dependent carrier trapping during off-state degradation for GaN based metal oxide semiconductor high electron mobility transistors. Journal of Applied Physics, 2018, 124, 165704.	1.1	3
11	Geometric contribution leading to anomalous estimation of two-dimensional electron gas density in GaN based heterostructures. Journal of Applied Physics, 2018, 123, 205702.	1.1	3
12	Thermally grown Nb-oxide for GaN-based MOS-diodes. Applied Surface Science, 2022, 572, 151332.	3.1	3
13	High-Performance GaN HEMTs with <i>I</i> _{ON} / <i>I</i> _{OFF} ¹⁰ and Gate Leakage Current ¹¹ Using Ta ₂ O ₅ Dielectric. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100839.	0.8	0